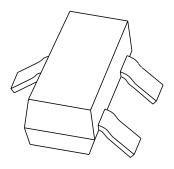
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBD6100 High-speed double diode

Product specification Supersedes data of November 1993 File under Discrete Semiconductors, SC01 1996 Apr 19





High-speed double diode

PMBD6100

FEATURES

- Small plastic SMD package
- · High switching speed: max. 4 ns
- · General application
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 450 mA
- Forward voltage: max. 1.1 V.

APPLICATIONS

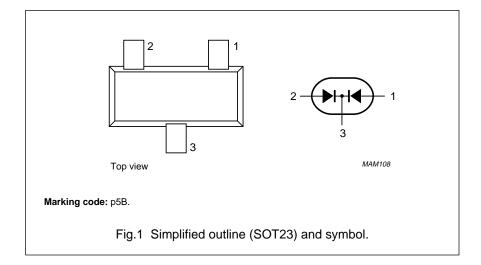
 High-speed switching in surface mounted circuits.

DESCRIPTION

The PMBD6100 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the small plastic SMD SOT23 package.

PINNING

PIN	DESCRIPTION	
1	anode (a1)	
2	anode (a2)	
3	common cathode	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per diode	Per diode					
V _{RRM}	repetitive peak reverse voltage		_	85	V	
V _R	continuous reverse voltage		_	70	V	
I _F	continuous forward current	single diode loaded; see Fig.2; note 1	_	215	mA	
		double diode loaded; see Fig.2; note 1	_	125	mA	
I _{FRM}	repetitive peak forward current		_	450	mA	
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4				
		t = 1 μs	_	4	A	
		t = 1 ms	_	1	A	
		t = 1 s	_	0.5	A	
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	250	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	

Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

PMBD6100

ELECTRICAL CHARACTERISTICS

 T_j = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode	Per diode				
V _F	forward voltage	see Fig.3			
		I _F = 1 mA	550	700	mV
		I _F = 10 mA	_	855	mV
		I _F = 50 mA	_	1.0	V
		I _F = 100 mA	0.85	1.1	V
I _R	reverse current	see Fig.5			
		V _R = 50 V	_	100	nA
		V _R = 50 V; T _j = 150 °C	_	50	μΑ
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	_	1.5	pF
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	-	4	ns
V _{fr}	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	_	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		360	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

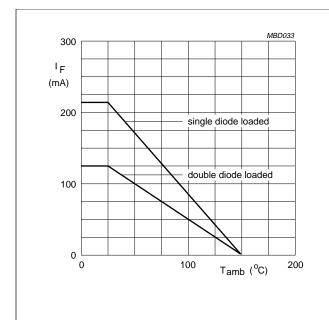
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

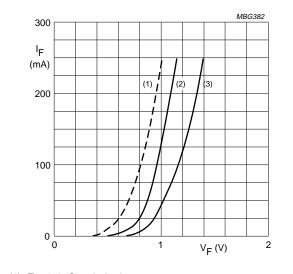
PMBD6100

GRAPHICAL DATA



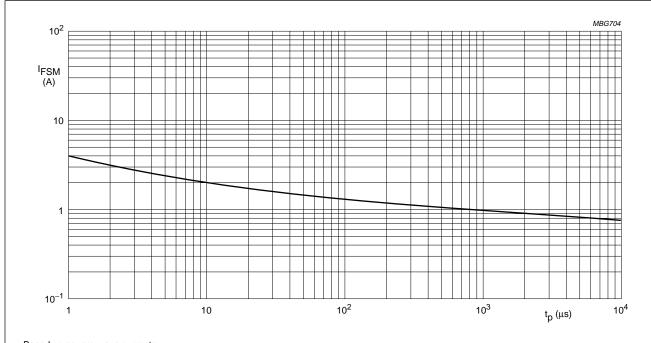
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_i = 150$ °C; typical values.
- (2) $T_i = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



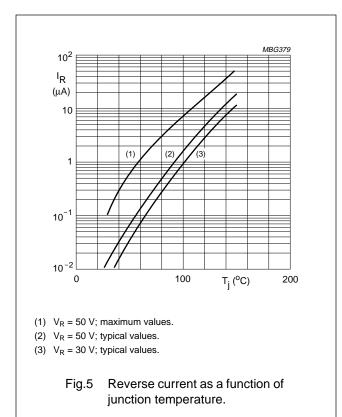
Based on square wave currents.

 T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

High-speed double diode

PMBD6100



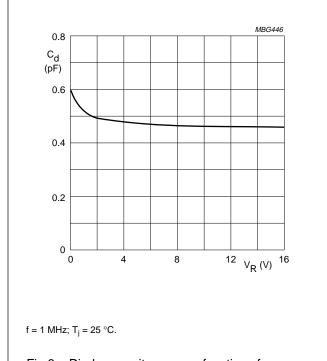
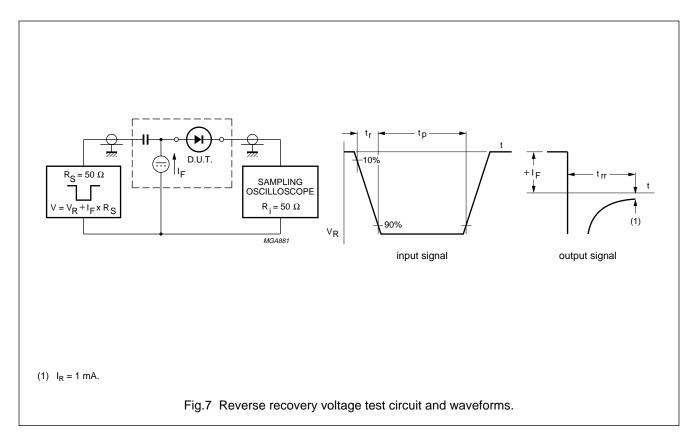


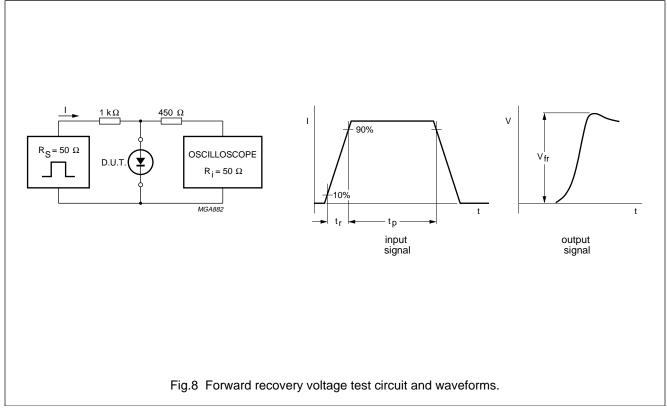
Fig.6 Diode capacitance as a function of reverse voltage; typical values.

5

High-speed double diode

PMBD6100

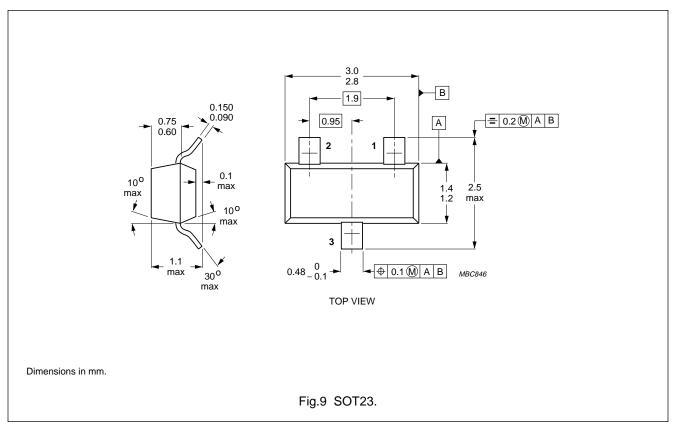




High-speed double diode

PMBD6100

PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.